

MOSFETs Silicon 650V N-Channel MOS
■ Applications

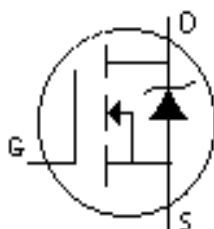
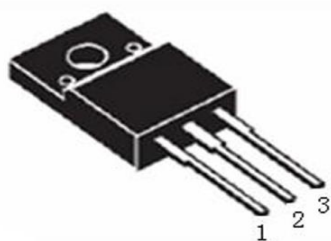
- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)

■ Features

- Low $R_{DS(ON)}$
- Ultra Low Gate Charge
- RoHS Compliant
- 100% UIS and RG Tested

■ Product Summary

V_{DS}	650	V
I_D	10	A
$R_{DS(ON)}, Typ@10V$	0.8	Ω
Q_g	30	nC



Gate: 1
Drain: 2
Source: 3

TO-220F

Marking	Package	Packaging	Min. package quantity
MHFIRF10N65M	TO-220F	Tube	1000



■ Absolute Maximum Ratings (Tc=25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	650	V
Gate-Source Voltage	V_{GS}	±30	V
Continuous Drain Current (Note 1)	I_D	10	A
Drain Current-Pulsed (Note 1)	I_{DM}	40	A
Total Dissipation	P_D	50	W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{stg}	-55-150	°C
Single Pulse Avalanche Energy (Note 2)	E_{AS}	820	mJ

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

■ Thermal Characteristics

Parameter	Symbol	Max	Unit
Maximum Junction-to-Case	$R_{\theta JC}$	2.5	°C/W
Maximum Junction-to-Ambient	$R_{\theta JA}$	80	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: $V_{DD}=50V$, $T_{ch}=25^{\circ}C$ (initial), $I_{AS}=10A$, $R_g=25\Omega$.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

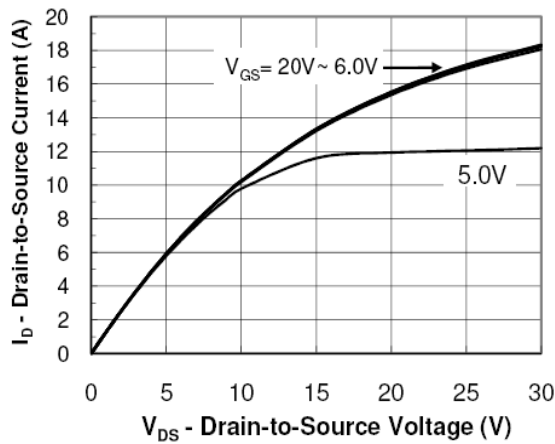


■ Electrical Characteristics (Tc=25°C unless otherwise noted)

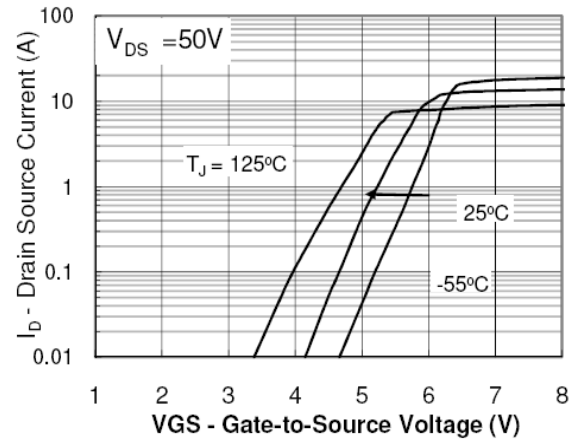
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static Parameters						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	650	-	-	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =650V,V _{GS} =0V	-	-	1	uA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±30V,V _{DS} =0V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} ,I _D =250uA	2	3	4	V
Drain-Source On Resistance	R _{DS(ON)}	V _{GS} =10V,I _D =5A	-	0.8	1	Ω
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} =25V,V _{GS} =0V, f=1.0MHz	-	1210	-	pF
Output Capacitance	C _{oss}		-	145	-	pF
Reverse Transfer Capacitance	C _{rss}		-	16	-	pF
Gate Resistance	R _g	V _{DS} =0V,V _{GS} =0V, f=1.0MHz	-	2.5	-	Ω
Switching Paramters						
Turn-On Delay Time	t _{d(on)}	V _{DS} =325V,I _D =10A, V _{GS} =10V,R _G =25Ω	-	20	-	ns
Turn-On Rise Time	t _r		-	30	-	ns
Turn-Off Delay Time	t _{d(off)}		-	90	-	ns
Turn-Off Rise Time	t _f		-	40	-	ns
Total Gate Charge	Q _g	V _{DS} =520V,I _D =10A, V _{GS} =10V	-	30	-	nC
Gate-Source Charge	Q _{gs}		-	5	-	nC
Gate-Drain Charge	Q _{gd}		-	14	-	nC
Source-Drain Characteristics						
Max. Diode Forward Cuurent	I _S		-	-	10	A
Max. Pulsed Forward Cuurent	I _{SM}		-	-	40	A
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =10A	-	0.92	1.5	V
Reverse Recovery Time	t _{rr}	V _R =400V,I _F =10A, di/dt=100A/us	-	450	-	ns
Reverse Recovery Charge	Q _{rr}		-	4.2	-	μC



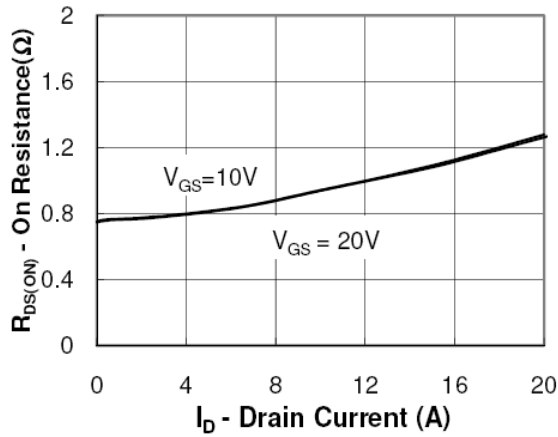
■ Characteristics Curves



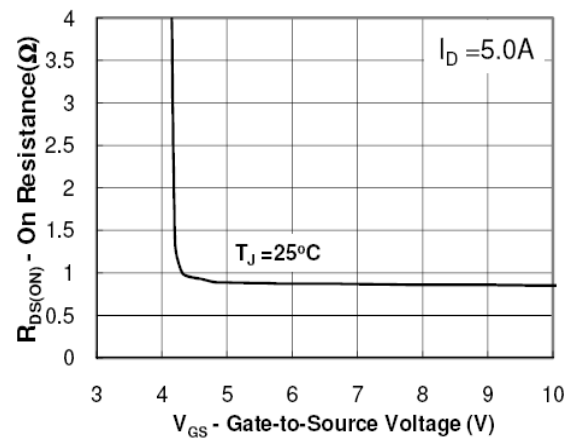
Output Characteristics



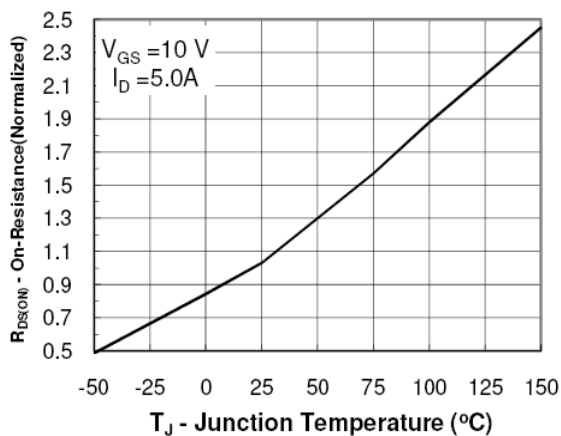
Transfer Characteristics



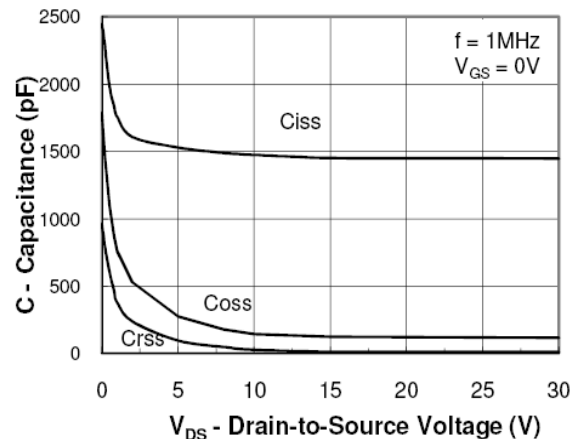
On Resistance Vs Drain Current



On Resistance Vs Gate Source Voltage

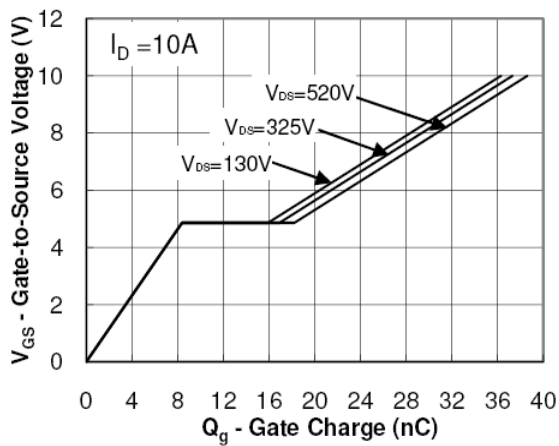
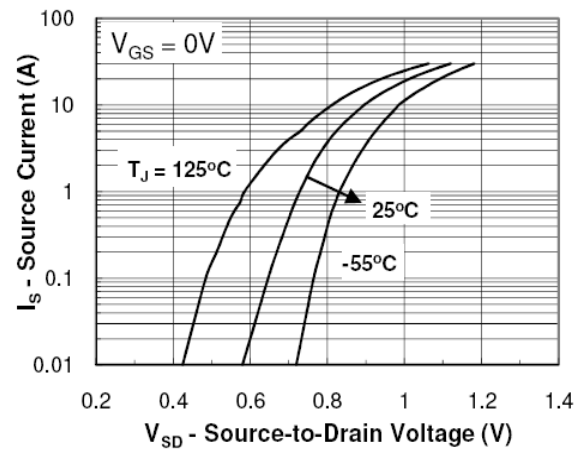
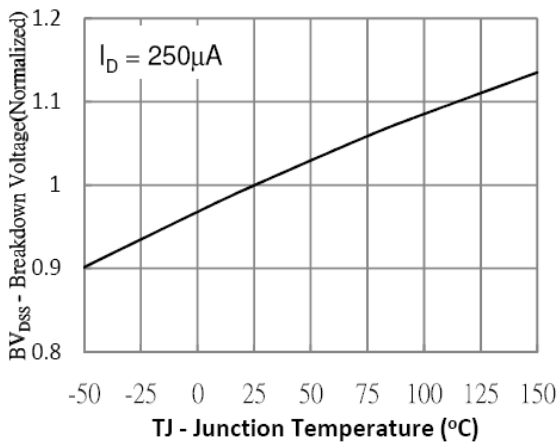


Rdson-JunctionTemperature



Capacitance



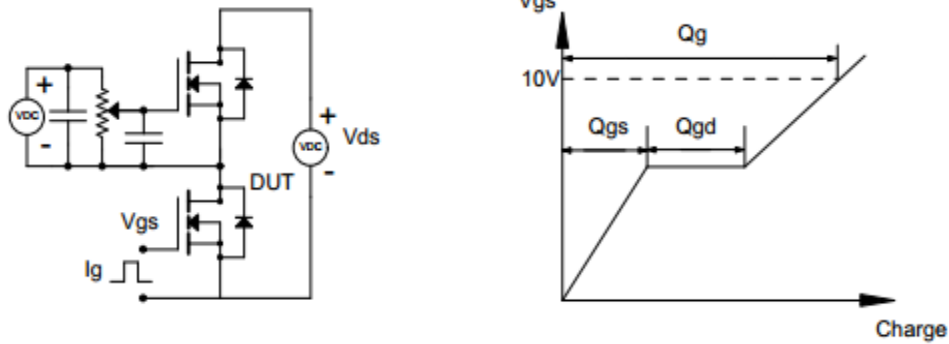
**Gate Charge Waveform****Source-Drain Diode Forward Voltage****Breakdown Voltage Vs Junction Temperature**

Note : The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

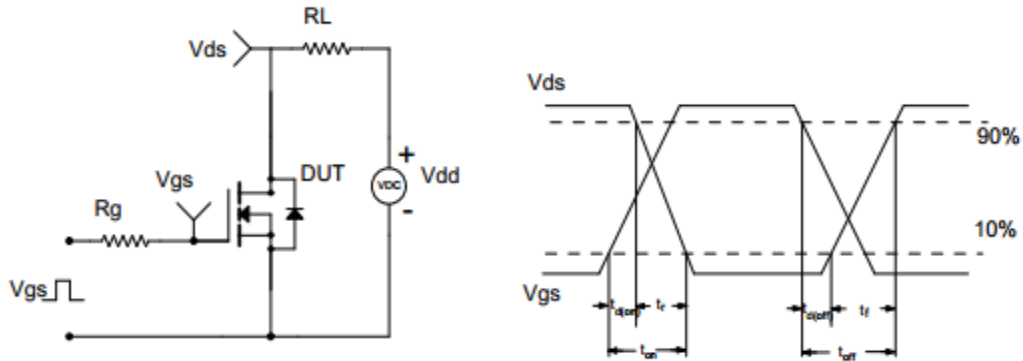


■ Test Circuit & Waveform

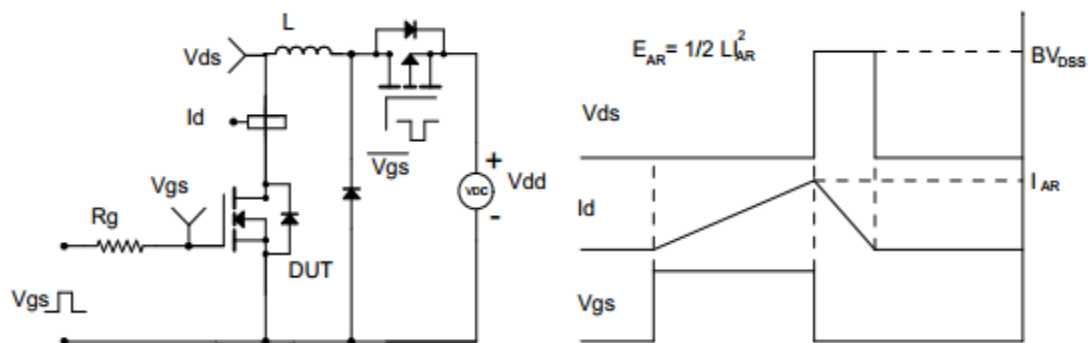
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveform



Unclamped Inductive Switching (UIS) Test Circuit & Waveform



■ TO-220F Package Dimensions

Unit: mm

Symbol	Min	Nom	Max	Symbol	Min	Nom	Max
A	4.5		4.9	E1	6.5	7	7.5
A1	2.3		2.9	e	2.44	2.54	2.64
b	0.65		0.9	L	12.5		14.3
b1	1.1		1.7	L1	9.45		10.05
b2	1.2		1.4	L2	15		16
c	0.35		0.65	L3	3.2		4.4
D	14.5		16.5	ΦP	3		3.3
D1	6.1		6.9	Q	2.5		2.9
E	9.6		10.3				

